
2SJ552(L), 2SJ552(S)

Silicon P Channel MOS FET
High Speed Power Switching

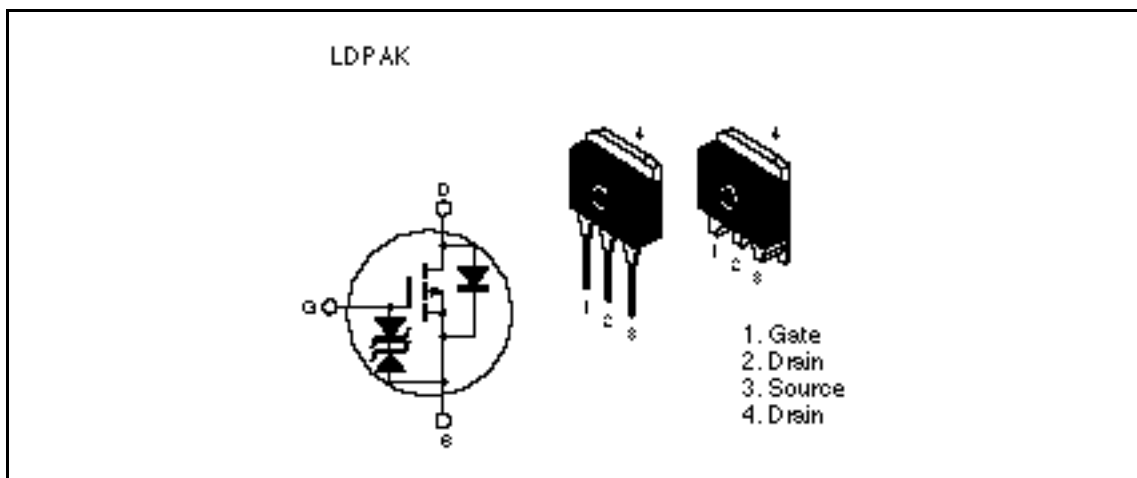
HITACHI

ADE-208-651B (Z)
3rd. Edition
Jun 1998

Features

- Low on-resistance
 $R_{DS(on)} = 0.042 \text{ typ.}$
- Low drive current.
- 4V gate drive devices.
- High speed switching.

Outline



2SJ552(L),2SJ552(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-60	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	-20	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	-80	A
Body-drain diode reverse drain current	I_{DR}	-20	A
Avalanche current	I_{AP} ^{Note3}	-20	A
Avalanche energy	E_{AR} ^{Note3}	34	mJ
Channel dissipation	P_{ch} ^{Note2}	75	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

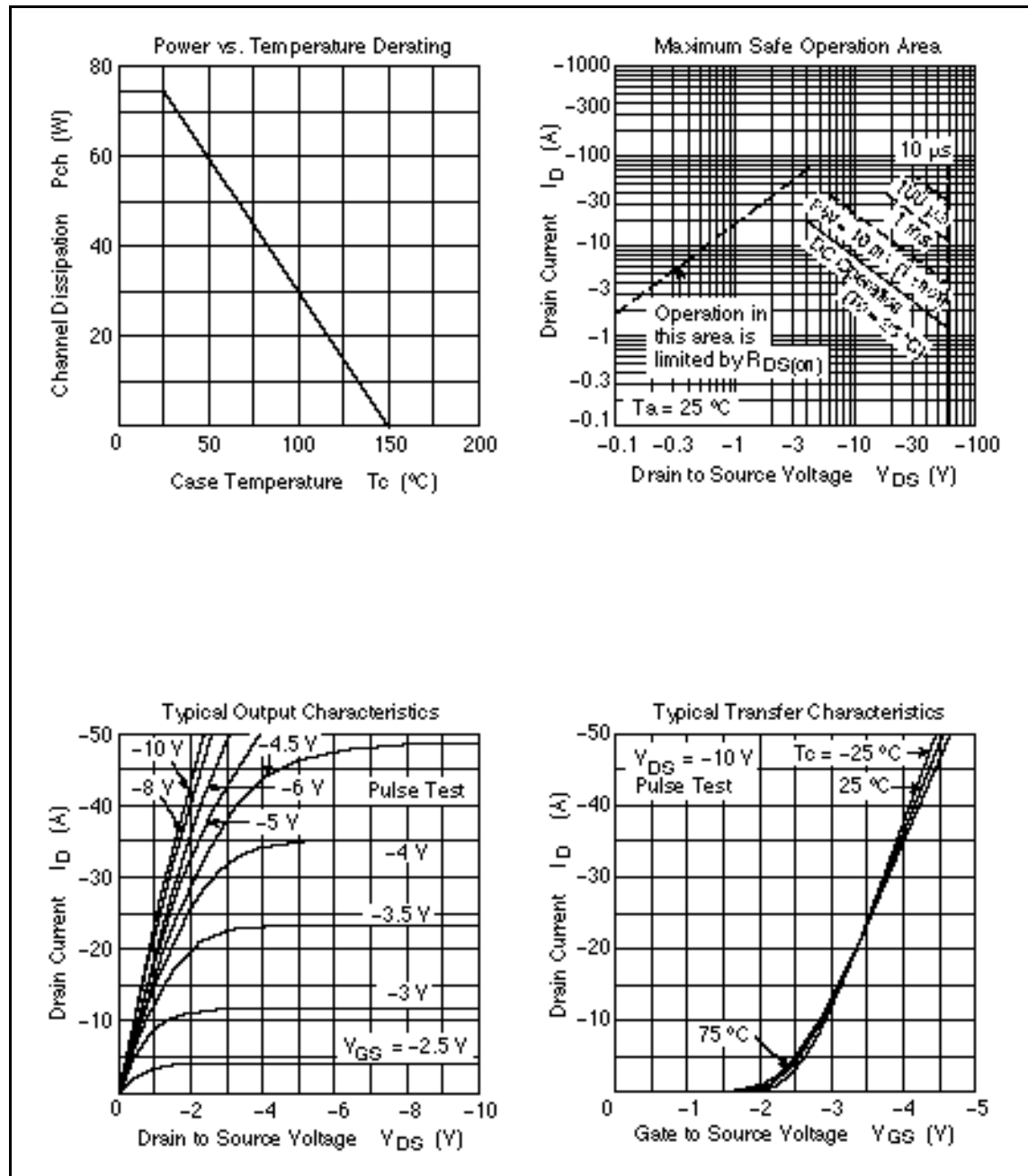
Note: 1. PW 10μs, duty cycle 1 %
2. Value at Tc = 25°C
3. Value at Tch = 25°C, Rg 50

Electrical Characteristics (Ta = 25°C)

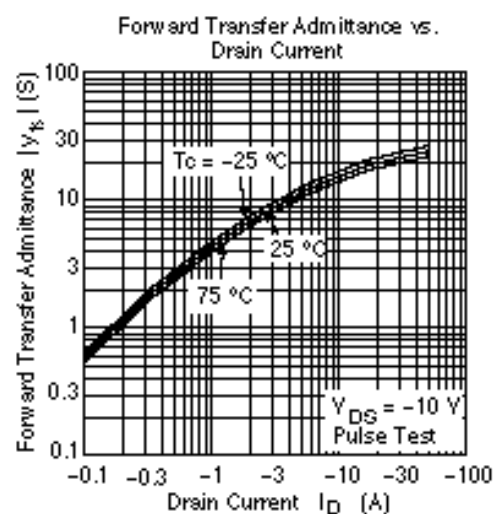
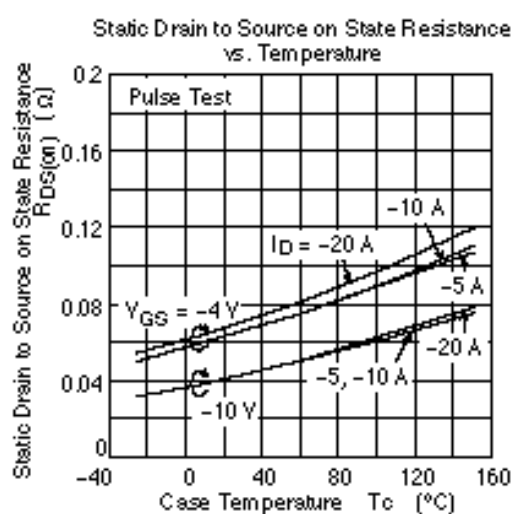
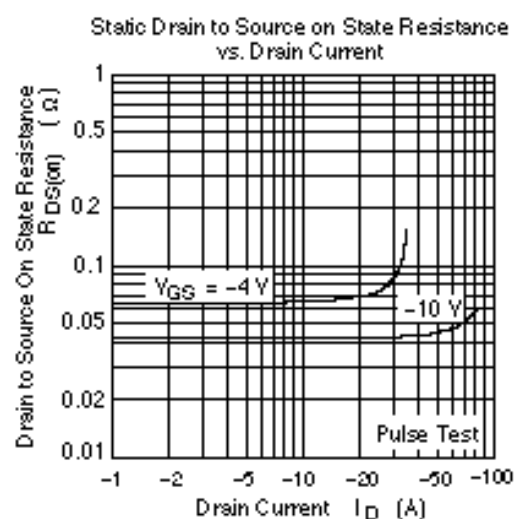
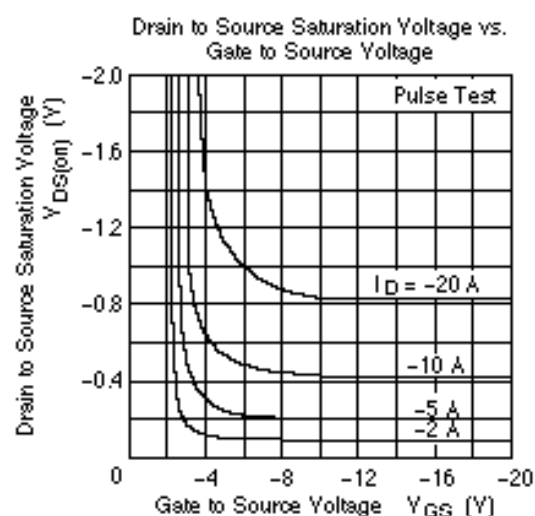
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100\mu A, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-10	μA	$V_{DS} = -60V, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1mA, V_{DS} = -10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.042	0.055		$I_D = -10A, V_{GS} = -10V$ ^{Note4}
	$R_{DS(on)}$	—	0.065	0.095		$I_D = -10A, V_{GS} = -4V$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	10	16	—	S	$I_D = -10A, V_{DS} = -10V$ ^{Note4}
Input capacitance	C_{iss}	—	1750	—	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	—	800	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	180	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	16	—	ns	$V_{GS} = -10V, I_D = -10A$
Rise time	t_r	—	100	—	ns	$R_L = 3$
Turn-off delay time	$t_{d(off)}$	—	230	—	ns	
Fall time	t_f	—	140	—	ns	
Body-drain diode forward voltage	V_{DF}	—	-1.0	—	V	$I_F = -20A, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	100	—	ns	$I_F = -20A, V_{GS} = 0$ $di_F/dt = 50A/\mu s$

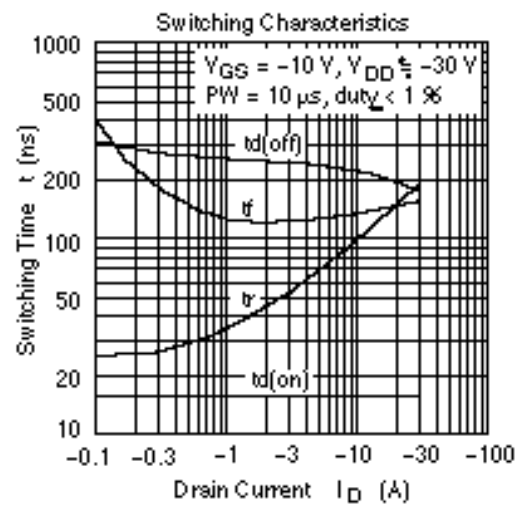
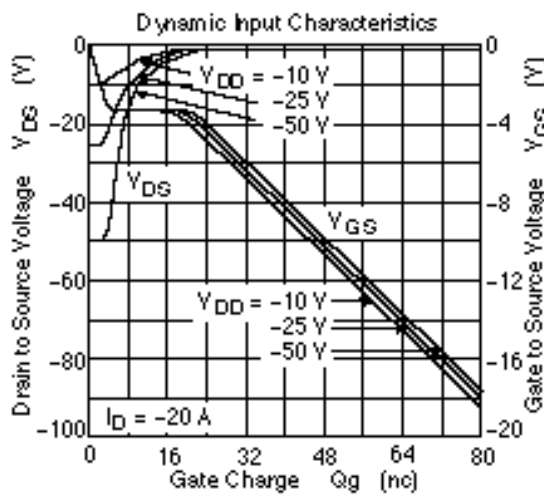
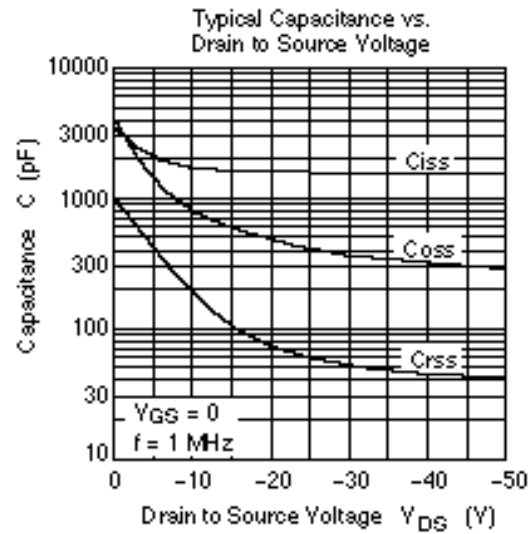
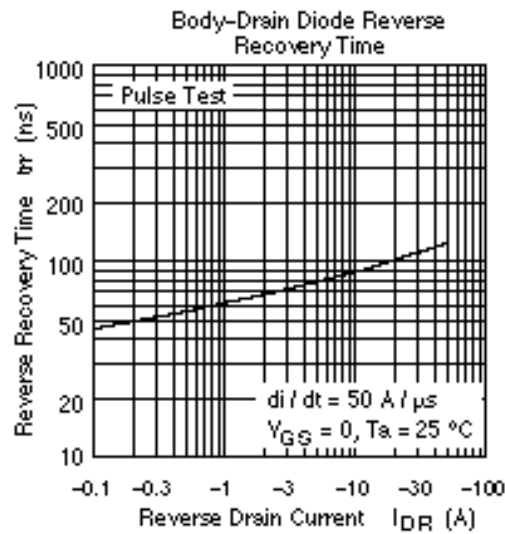
Note: 4. Pulse test

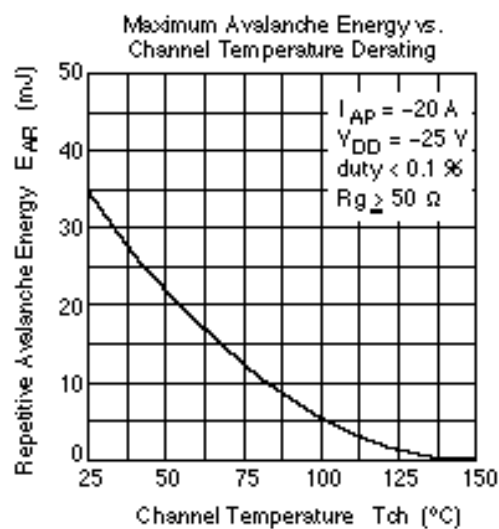
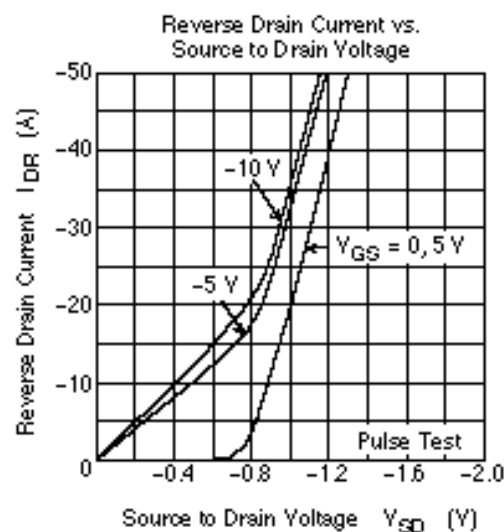
Main Characteristics



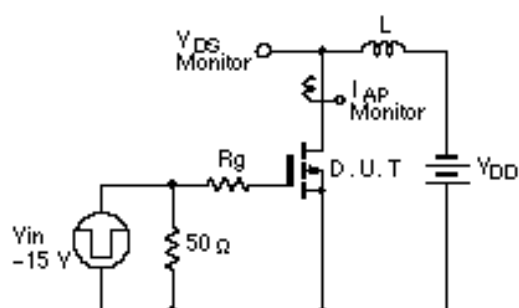
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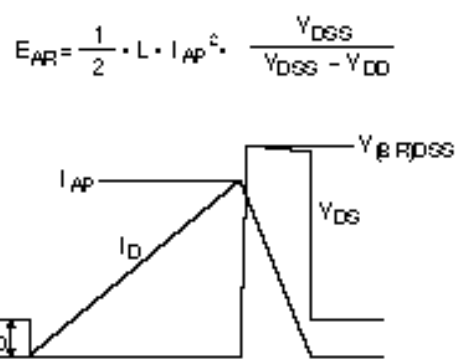


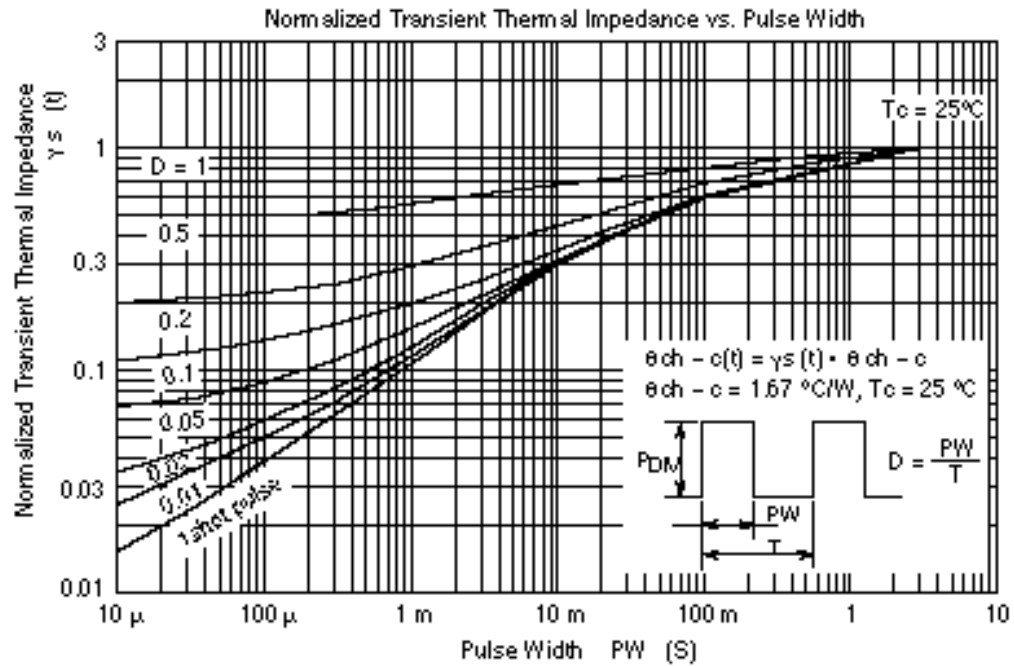


Avalanche Test Circuit

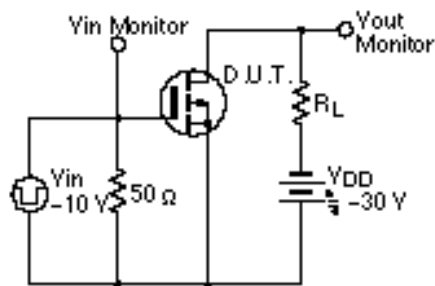


Avalanche Waveform

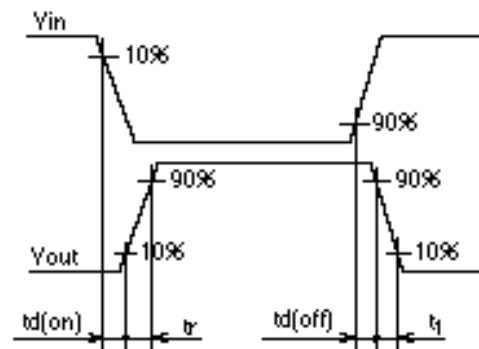




Switching Time Test Circuit



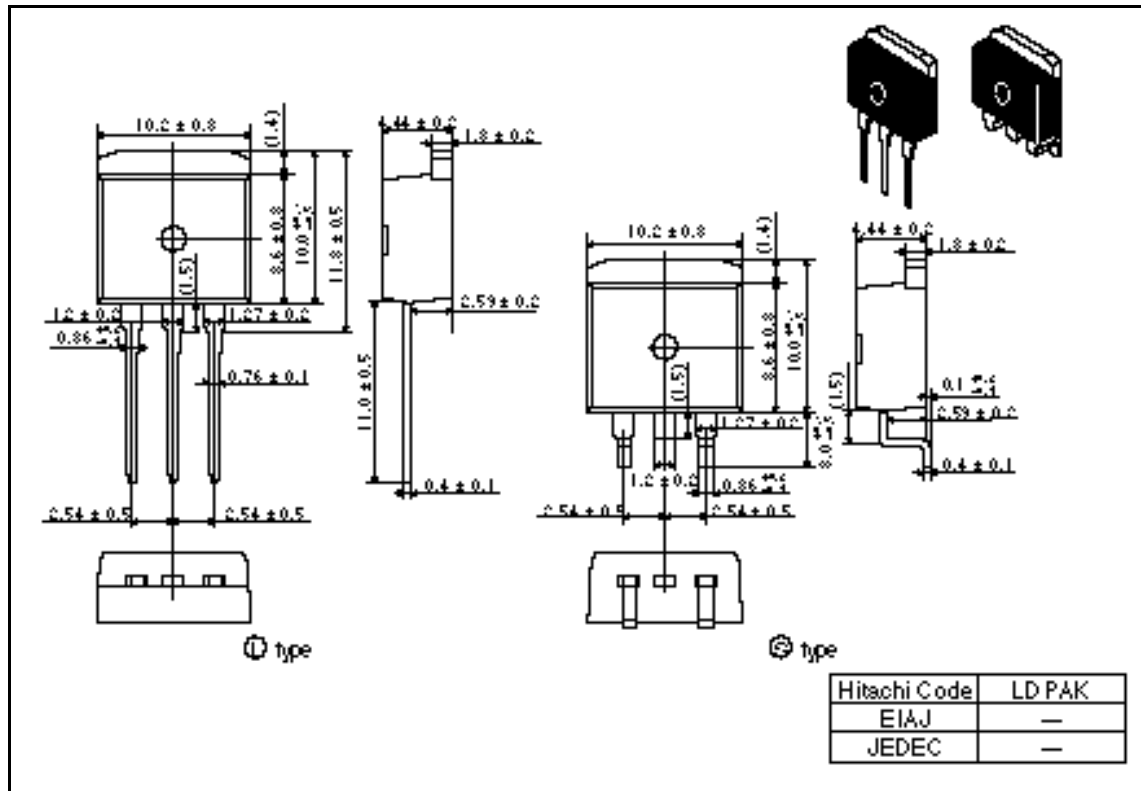
Waveform



2SJ552(L),2SJ552(S)

Package Dimensions

Unit: mm



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HITACHI

Hitachi, Ltd.

Semiconductor S. I.C. Div.

Nippon Bldg., 2-6-2, Ohie-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 8270-2111

Fax: (03) 8270-5109

For further information write to:

Hitachi Semiconductor
(America) Inc.

2000 Sierra Point Parkway
Brisbane, CA 94005-1897
U.S.A.

Tel: 800-285-1601

Fax: 808-297-0447

Hitachi Europe GmbH
Continental Europe

Domacher Straße 8
D-85622 Feldkirchen
München

Tel: 089-991 80-0

Fax: 089-929 80-00

Hitachi Europe Ltd.

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

M Maidenhead

Berkshire SL6 8YA

United Kingdom

Tel: 01628-585000

Fax: 01628-585160

Hitachi Asia Pte. Ltd.

16 Collyer Quay #20-00

Hitachi Tower

Singapore 043818

Tel: 535-2100

Fax: 535-1538

Hitachi Asia (Hong Kong) Ltd.

Unit 1706, North Tower,

World Finance Centre,

Harbour City Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel: 27859218

Fax: 27806071

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